P-Channel Power MOSFET

FEATURES

- Advance trench process technology
- High density cell design for ultra-low on-resistance
- RoHS compliant
- Halogen-free

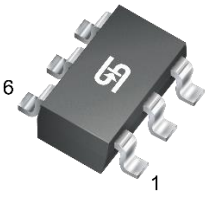
APPLICATIONS

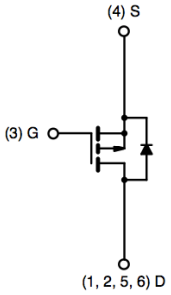
- Power management
- Load switch

KEY PERFORMANCE PARAMETERS			
PARAMETER		**VALUE**	**UNIT**
V_{DS}		-30	V
$R_{DS(on)}$ (max)	V_{GS} = -10V	48	mΩ
	V_{GS} = -4.5V	79	
Q_g		24	nC

Pb-Free RoHS COMPLIANT HALOGEN FREE

SOT-26





Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A = 25°C	I_D	-4.6	A
Pulsed Drain Current (Note 1)		I_{DM}	-18.4	A
Total Power Dissipation	T_A = 25°C	P_D	1.56	W
	T_A = 70°C		1	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	°C

THERMAL PERFORMANCE			
PARAMETER	**SYMBOL**	**LIMIT**	**UNIT**
Junction to Ambient Thermal Resistance (Note 2)	$R_{\Theta JA}$	80	°C/W

Notes:

1. Pulse Width ≤ 100μs.
2. Device on a PCB FR4 with 1 in^2 (single layer, 2 oz thickness) copper area for drain connection.

ELECTRICAL SPECIFICATIONS (T_A = 25°C unless otherwise noted)						
PARAMETER	**CONDITIONS**	**SYMBOL**	**MIN**	**TYP**	**MAX**	**UNIT**
Static (Note 3)						
Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = -250μA	BV_{DSS}	-30	--	--	V
Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250μA	$V_{GS(TH)}$	-1	-1.5	-3	V
Gate Body Leakage	V_{GS} = ±20V, V_{DS} = 0V	I_{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V_{DS} = -24V, V_{GS} = 0V	I_{DSS}	--	--	-1	μA
Drain-Source On-State Resistance	V_{GS} = -10V, I_D = -4.6A	$R_{DS(on)}$	--	15	48	mΩ
	V_{GS} = -4.5V, I_D = -3.6A		--	21	79	
Forward Transconductance	V_{DS} = -10V, I_D = -1.2A	g_{fs}	--	7	--	S
Dynamic (Note 4)						
Total Gate Charge	V_{DS} = -15V, I_D = -4.6A, V_{GS} = -10V	Q_g	--	24	--	nC
Gate-Source Charge		Q_{gs}	--	3.3	--	
Gate-Drain Charge		Q_{gd}	--	5.2	--	
Input Capacitance	V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz	C_{iss}	--	1077	--	pF
Output Capacitance		C_{oss}	--	188	--	
Reverse Transfer Capacitance		C_{rss}	--	29	--	
Switching (Note 5)						
Turn-On Delay Time	V_{DD} = -15V, R_G = 6Ω, I_D = -4.6A, V_{GS} = -10V	$t_{d(on)}$	--	5.6	--	ns
Turn-On Rise Time		t_r	--	2.3	--	
Turn-Off Delay Time		$t_{d(off)}$	--	95	--	
Turn-Off Fall Time		t_f	--	48	--	
Source-Drain Diode						
Forward Voltage (Note 3)	I_S = -4.6A, V_{GS} = 0V	V_{SD}	--	0.8	1.2	V

Notes:

3. Pulse test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.
4. Defined by design. Not subject to production test.
5. Switching time is essentially independent of operating temperature.

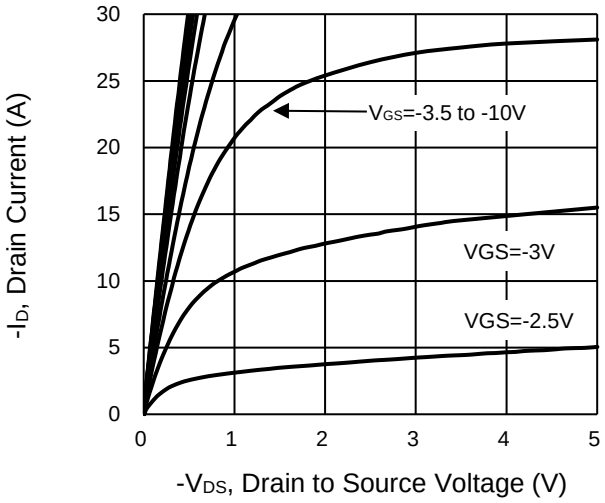
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM3481CX6 RFG	SOT-26	3kpcs / 7” Reel

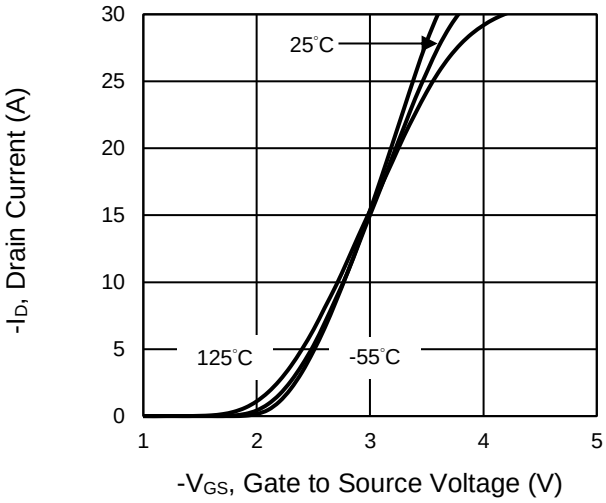
CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

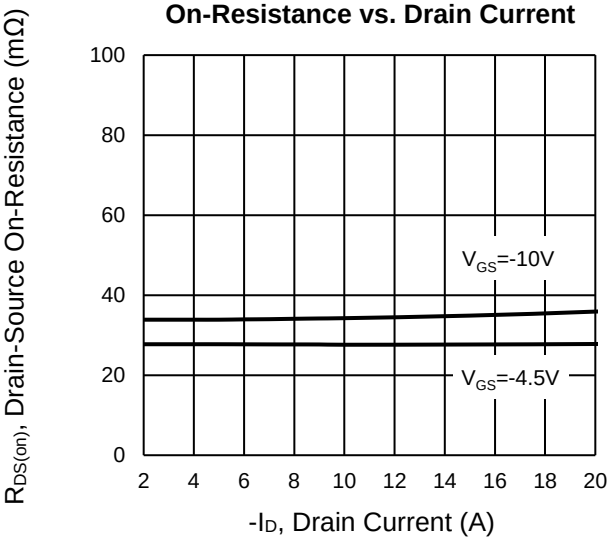
Output Characteristics



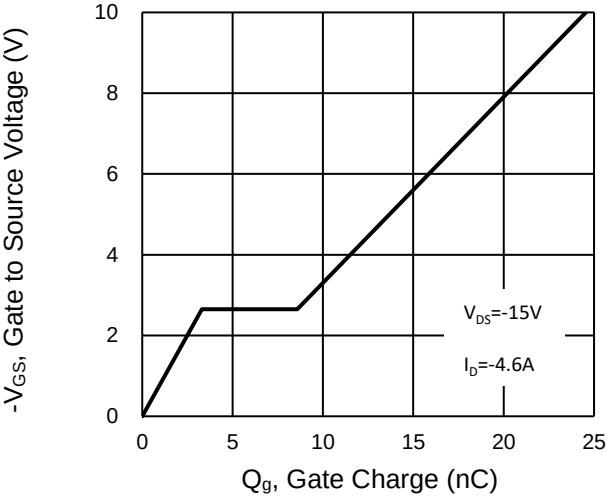
Transfer Characteristics



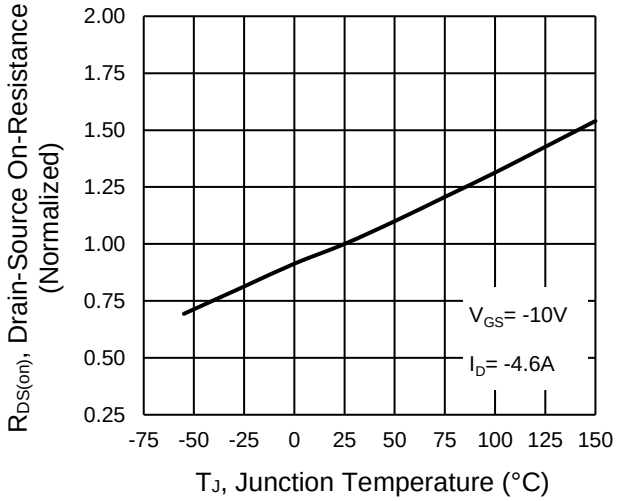
On-Resistance vs. Drain Current



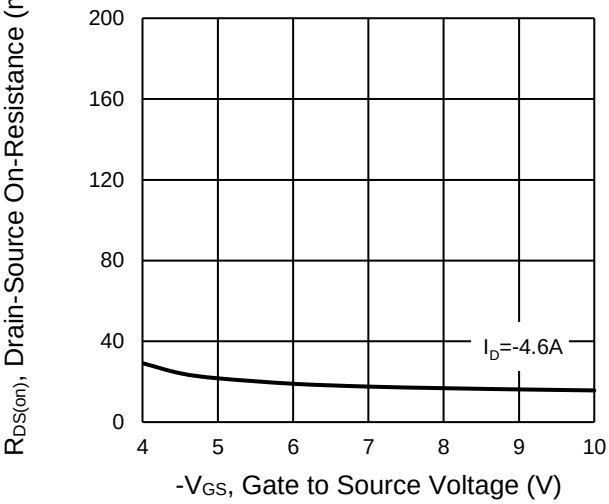
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



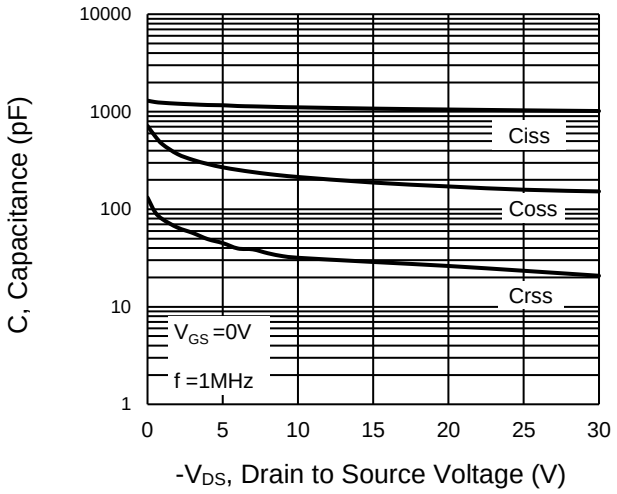
On-Resistance vs. Gate-Source Voltage



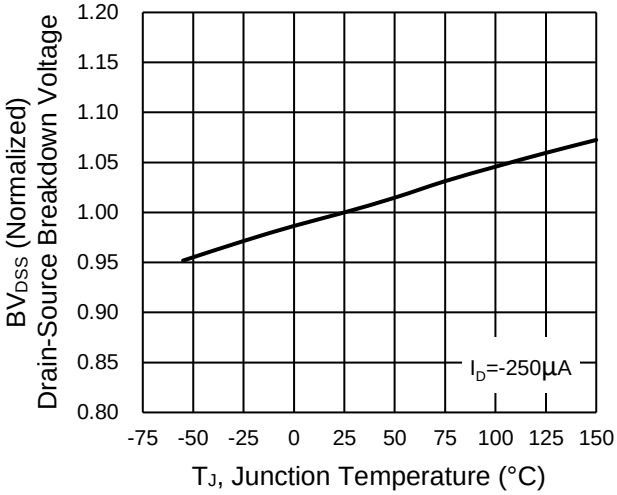
CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

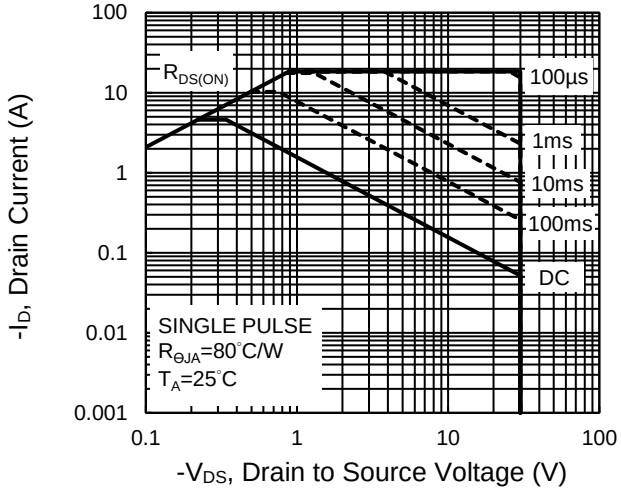
Capacitance vs. Drain-Source Voltage



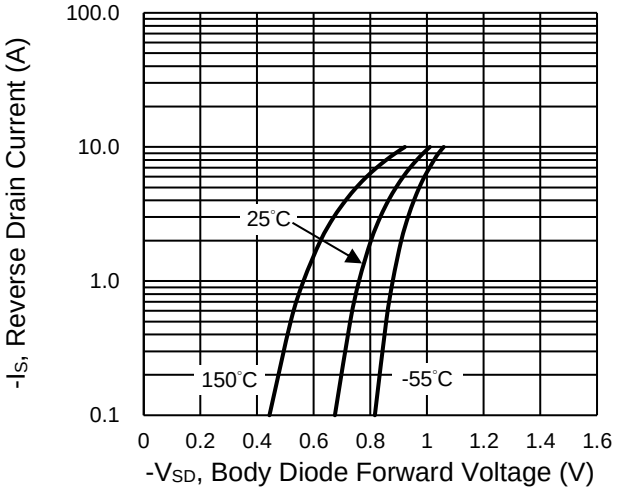
BV_{DSS} vs. Junction Temperature



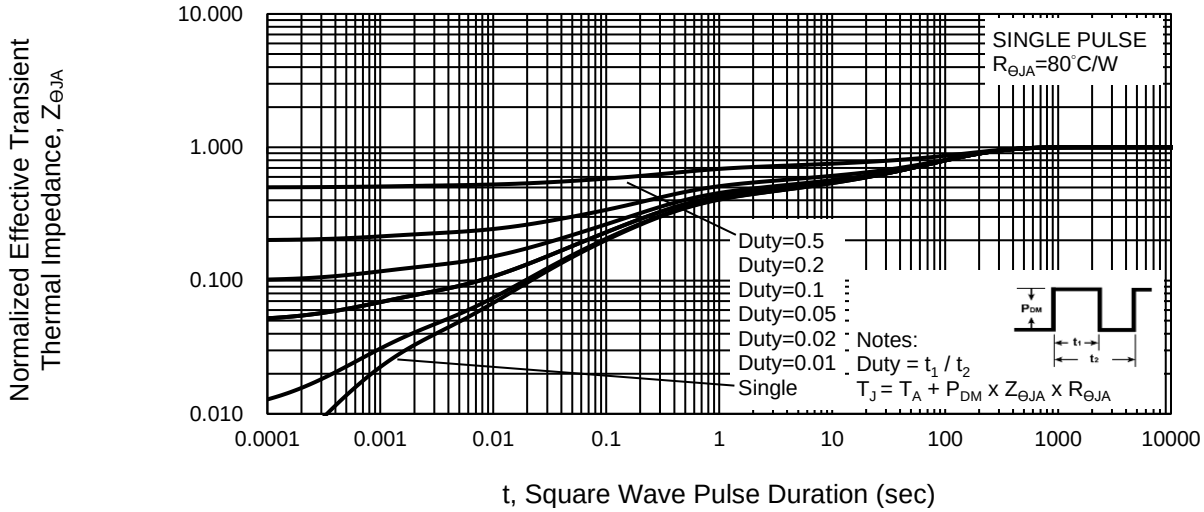
Maximum Safe Operating Area, Junction-to-Ambient



Source-Drain Diode Forward Current vs. Voltage



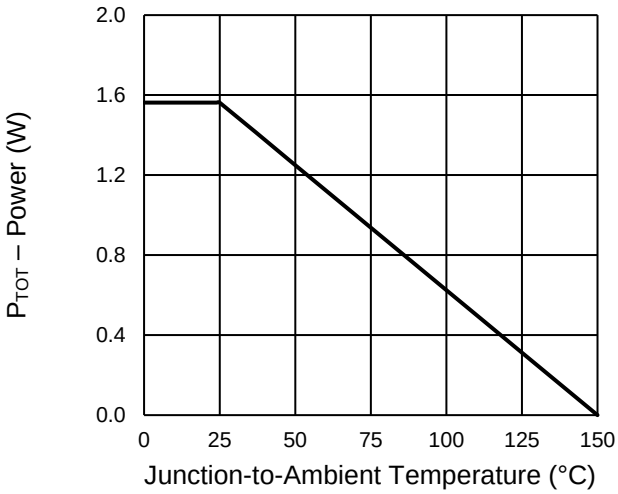
Normalized Thermal Transient Impedance, Junction-to-Ambient



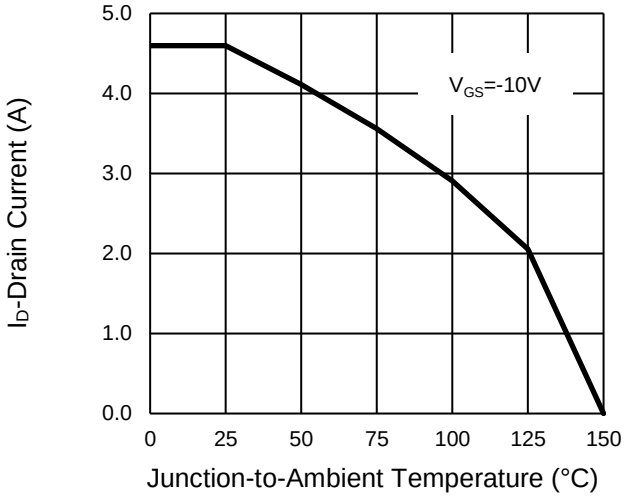
CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

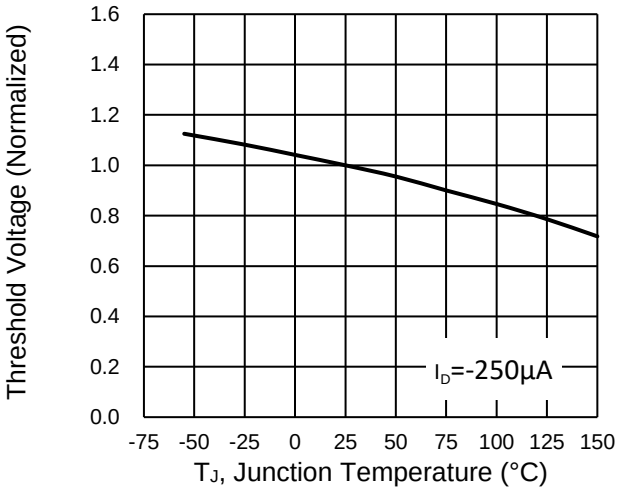
Power Dissipation



Drain Current

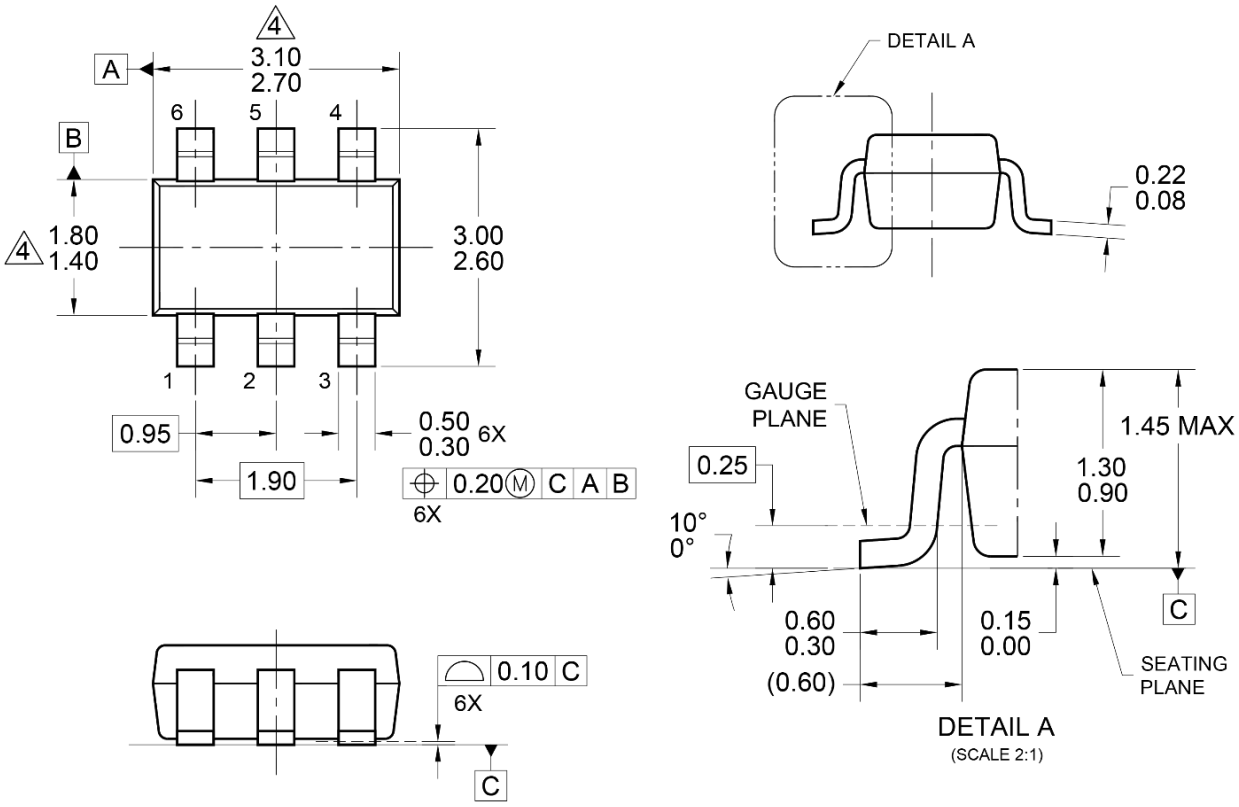


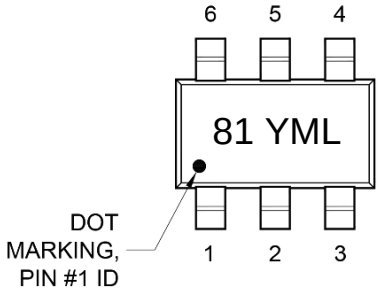
Normalized gate threshold voltage vs Temperature



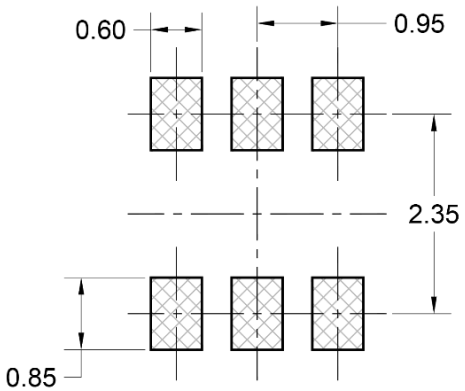
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

SOT-26





MARKING DIAGRAM



SUGGESTED PAD LAYOUT

81 = Device marking
Y = Year Code
M = Month Code for Halogen Free Product
(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
L = Lot Code

NOTES: UNLESS OTHERWISE SPECIFIED

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3. PACKAGE OUTLINE REFERENCE: JEDEC MO-178, VARIATION AB.
4. MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DWG NO. REF: HQ2SD07-SOT26-027 REV A.

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Purchasers are solely responsible for the choice, selection, and use of TSC products and TSC assumes no liability for application assistance or the design of Purchasers' products.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.